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(54) Title: DIES PREPEELING APPARATUS AND METHOD

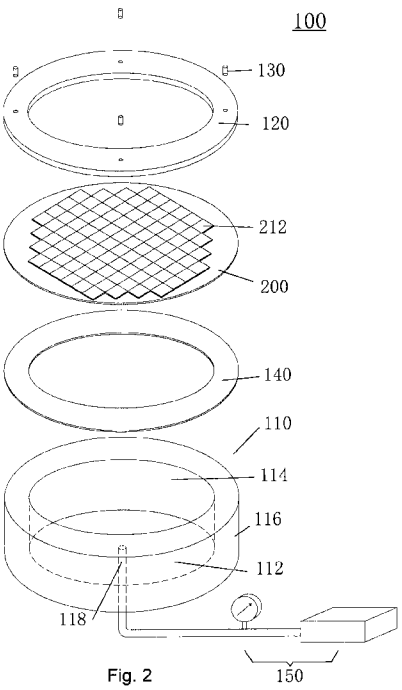


Fig. 2

(57) Abstract: An apparatus (100) and a method for prepeeling semiconductor dies (212) from a dicing tape (200) with the semiconductor dies (212) attached thereon are disclosed. The apparatus (100) comprises a chamber (110) having a bottom base (112), a top opening (114) and an annular sidewall (116) extended upward from the periphery of the base (112). The sidewall (116) has a substantially flat top surface. The apparatus (100) further comprises a cover (120) disposed above the chamber (110). The cover (120) has a central opening. The apparatus (100) further comprises at least one inlet (118) disposed in the base (112) and a pressure regulator (150) connected to the chamber (110) via the at least one inlet (118). The dicing tape (200) is disposed between the cover (120) and the top surface of the sidewall (116) to hermetically seal the top opening (114) of the chamber (110). The semiconductor dies (212) are located directly above the top opening (114) of the chamber (110).

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